

# Monica De Seta

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6664267/publications.pdf>

Version: 2024-02-01

20  
papers

279  
citations

759233

12  
h-index

888059

17  
g-index

20  
all docs

20  
docs citations

20  
times ranked

300  
citing authors

#	ARTICLE	IF	CITATIONS
1	On-chip infrared photonics with Si-Ge-heterostructures: What is next?. APL Photonics, 2022, 7, .	5.7	18
2	THz intersubband electroluminescence from n-type Ge/SiGe quantum cascade structures. Applied Physics Letters, 2021, 118, .	3.3	15
3	THz intersubband absorption in n-type Si <sup>111</sup> Ge parabolic quantum wells. Applied Physics Letters, 2021, 118, .	3.3	8
4	Terahertz intersubband electroluminescence from n-type germanium quantum wells. , 2021, , .		0
5	Tuning the Doping of Epitaxial Graphene on a Conventional Semiconductor via Substrate Surface Reconstruction. Journal of Physical Chemistry Letters, 2021, 12, 1262-1267.	4.6	4
6	Second Harmonic Generation in Germanium Quantum Wells for Nonlinear Silicon Photonics. ACS Photonics, 2021, 8, 3573-3582.	6.6	13
7	Electron Population Dynamics in Optically Pumped Asymmetric Coupled Ge/SiGe Quantum Wells: Experiment and Models. Photonics, 2020, 7, 2.	2.0	5
8	Disentangling elastic and inelastic scattering pathways in the intersubband electron dynamics of n-type Ge/SiGe quantum fountains. Physical Review B, 2020, 101, .	3.2	4
9	Intersubband Transition Engineering in the Conduction Band of Asymmetric Coupled Ge/SiGe Quantum Wells. Crystals, 2020, 10, 179.	2.2	11
10	Reduction of threading dislocation density beyond the saturation limit by optimized reverse grading. Physical Review Materials, 2020, 4, .	2.4	20
11	Terahertz absorption-saturation and emission from electron-doped germanium quantum wells. Optics Express, 2020, 28, 7245.	3.4	12
12	Submicron Size Schottky Junctions on As-Grown Monolayer Epitaxial Graphene on Ge(100): A Low-Invasive Scanned-Probe-Based Study. ACS Applied Materials & Interfaces, 2019, 11, 35079-35087.	8.0	7
13	Room temperature operation of n-type Ge/SiGe terahertz quantum cascade lasers predicted by non-equilibrium Green's functions. Applied Physics Letters, 2019, 114, .	3.3	45
14	Electron Dynamics in Silicon-Germanium Terahertz Quantum Fountain Structures. ACS Photonics, 2016, 3, 403-414.	6.6	17
15	Physical mechanisms of intersubband-absorption linewidth broadening in s-Ge/SiGe quantum wells. Physical Review B, 2014, 90, .	3.2	25
16	Combined effect of electron and lattice temperatures on the long intersubband relaxation times of Ge/SiGe quantum wells. Physical Review B, 2014, 89, .	3.2	14
17	Determination of the free carrier concentration in atomic-layer doped germanium thin films by infrared spectroscopy. Journal of Optics (United Kingdom), 2014, 16, 094010.	2.2	8
18	Onset of plastic relaxation in the growth of Ge on Si(001) at low temperatures: Atomic-scale microscopy and dislocation modeling. Physical Review B, 2013, 88, .	3.2	13

#	ARTICLE	IF	CITATIONS
19	X-ray diffraction study of plastic relaxation in Ge-rich SiGe virtual substrates. Physical Review B, 2012, 85, .	3.2	14
20	Long intersubband relaxation times in <i>n</i> -type germanium quantum wells. Applied Physics Letters, 2011, 99, .	3.3	26